

General Description

The MY4G06C uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

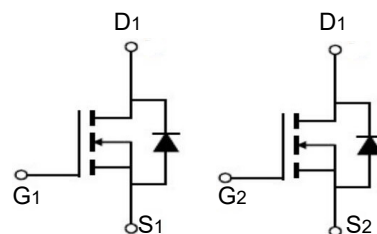
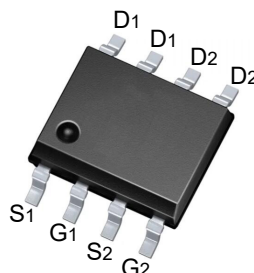


Features

V_{DSS}	60	-60	V
I_D	4	-3.7	A
$R_{DS(ON)}(at V_{GS}=10V)$	<45		m Ω
$R_{DS(ON)}(at V_{GS}=10V)$	<80		m Ω

Application

- Battery protection
- Load switch
- Uninterruptible power supply



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY4G06C	SOP-8	4G06C	3000

Absolute Maximum Ratings ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating		Units
		N-Channel	P-Channel	
V_{DS}	Drain-Source Voltage	60	-60	V
V_{GS}	Gate-Source Voltage	± 20	± 20	V
$I_{D@T_A=25^{\circ}\text{C}}$	Continuous Drain Current, $V_{GS} @ 10V^1$	4.8	-3.7	A
$I_{D@T_A=70^{\circ}\text{C}}$	Continuous Drain Current, $V_{GS} @ 10V^1$	3.8	-3	A
I_{DM}	Pulsed Drain Current ²	9.6	-7.5	A
EAS	Single Pulse Avalanche Energy ³	25.5	35.3	mJ
I_{AS}	Avalanche Current	22.6	-26.6	A
$P_{D@T_A=25^{\circ}\text{C}}$	Total Power Dissipation ⁴	1.5	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	-55 to 150	$^{\circ}\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	-55 to 150	$^{\circ}\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	85	$^{\circ}\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	36	$^{\circ}\text{C/W}$

N-Channel Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	0.063	---	$V/^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=4A$	30	---	45	$m\Omega$
		$V_{GS}=4.5V$, $I_D=2A$	50	---	70	
$V_{GS(th)}$	Gate Threshold Voltage		1.2	---	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient	$V_{GS}=V_{DS}$, $I_D=250\mu A$	---	-5.24	---	$mV/^{\circ}\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=48V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=48V$, $V_{GS}=0V$, $T_J=55^{\circ}\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=4A$	---	21	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1MHz$	---	3.2	---	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=48V$, $V_{GS}=4.5V$, $I_D=4A$	---	12.6	---	nC
Q_{gs}	Gate-Source Charge		---	3.2	---	
Q_{gd}	Gate-Drain Charge		---	6.3	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=30V$, $V_{GS}=10V$, $R_G=3.3\Omega$, $I_D=4A$	---	8	---	ns
T_r	Rise Time		---	14.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	24.4	---	
T_f	Fall Time		---	4.6	---	
C_{iss}	Input Capacitance	$V_{DS}=15V$, $V_{GS}=0V$, $f=1MHz$	---	500	---	pF
C_{oss}	Output Capacitance		---	39	---	
C_{rss}	Reverse Transfer Capacitance		---	27	---	
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	4.8	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	9.6	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=1A$, $T_J=25^{\circ}\text{C}$	---	---	1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=-25V$, $V_{GS}=-10V$, $L=0.1mH$, $I_{AS}=-26.6A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation

P-Channel Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-60	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C, I _D =-1mA	---	-0.03	---	V/°C
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-10V, I _D =-3A	60	---	80	mΩ
		V _{GS} =-4.5V, I _D =-2A	80	---	100	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.2	---	-2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	4.56	---	mV/°C
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-48V, V _{GS} =0V, T _J =25 °C	---	---	1	uA
		V _{DS} =-48V, V _{GS} =0V, T _J =55 °C	---	---	5	
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-3A	---	15	---	S
R _g	Gate Resistance	V _{DS} =0V, V _{GS} =0V, f=1MHz	---	13.5	---	Ω
Q _g	Total Gate Charge (-4.5V)	V _{DS} =-48V, V _{GS} =-4.5V, I _D =-3A	---	9.86	---	nC
Q _{gs}	Gate-Source Charge		---	3.1	---	
Q _{gd}	Gate-Drain Charge		---	2.95	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =-15V, V _{GS} =-10V, R _G =3.3Ω I _D =-1A	---	28.8	---	ns
T _r	Rise Time		---	19.8	---	
T _{d(off)}	Turn-Off Delay Time		---	60.8	---	
T _f	Fall Time		---	7.2	---	
C _{iss}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	---	1447	---	pF
C _{oss}	Output Capacitance		---	97.3	---	
C _{rss}	Reverse Transfer Capacitance		---	70	---	
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V, Force Current	---	---	-3.7	A
I _{SM}	Pulsed Source Current ^{2,5}		---	---	-7.5	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =-1A, T _J =25 °C	---	---	-1.2	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is VDD=25V,VGS=10V,L=0.1mH,IAS=22.6A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation

N-Channel Typical Characteristics

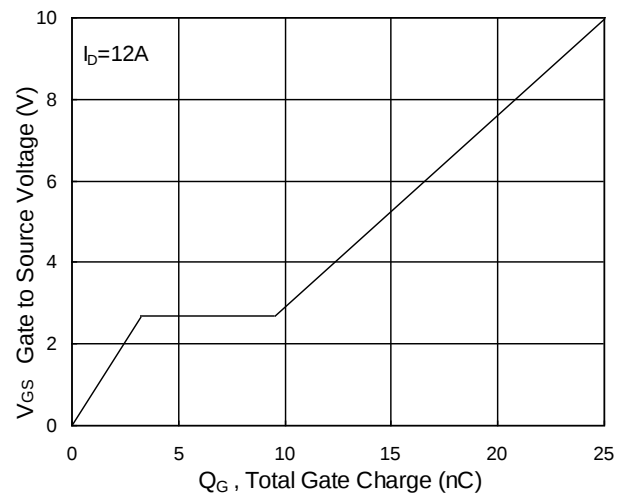
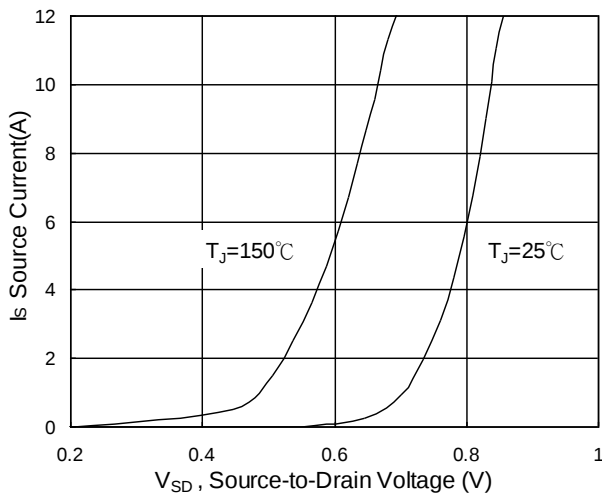
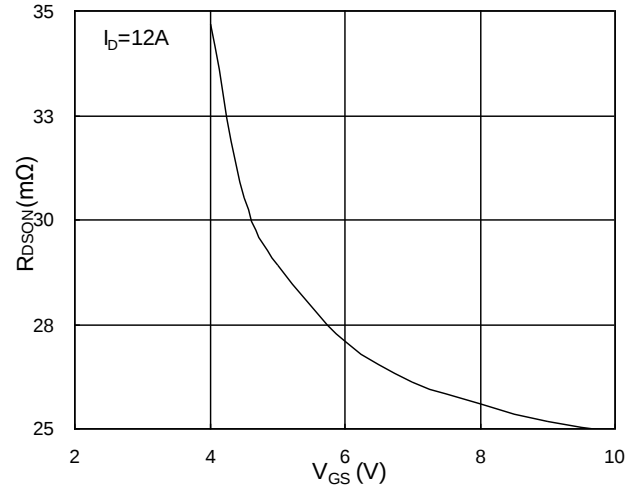
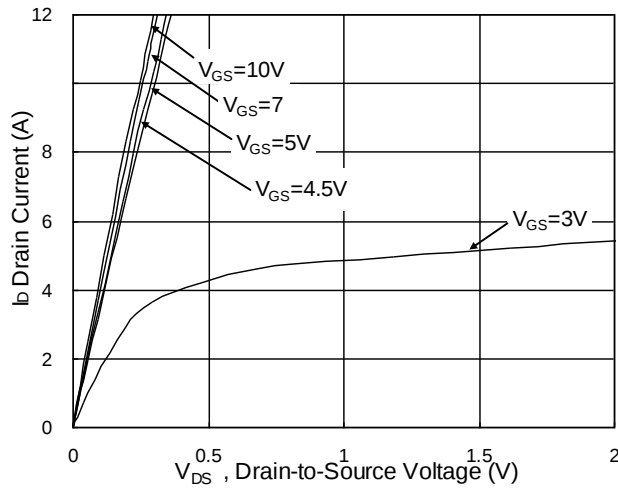
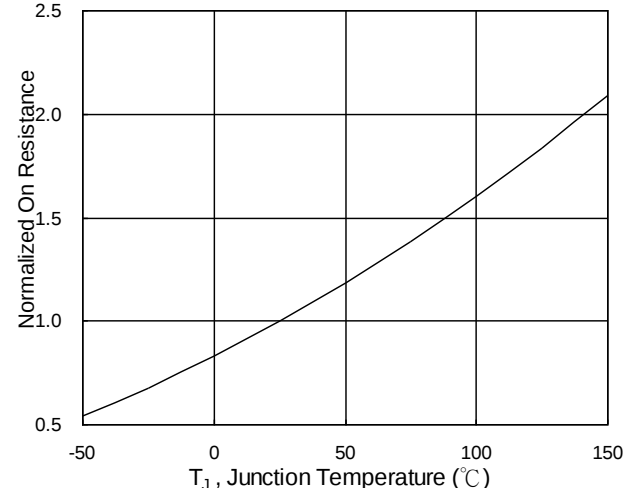
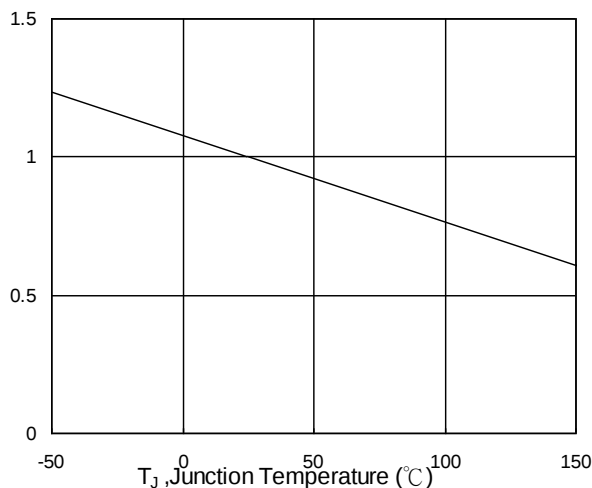


Fig.3 Forward Characteristics of Reverse

Fig.4 Gate-Charge Characteristics



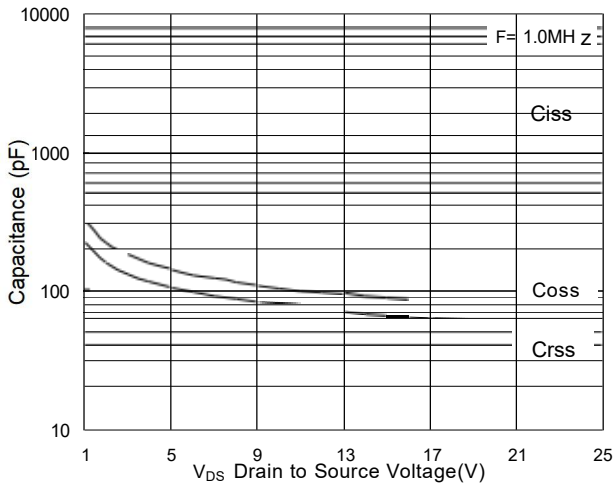


Fig.7 Capacitance

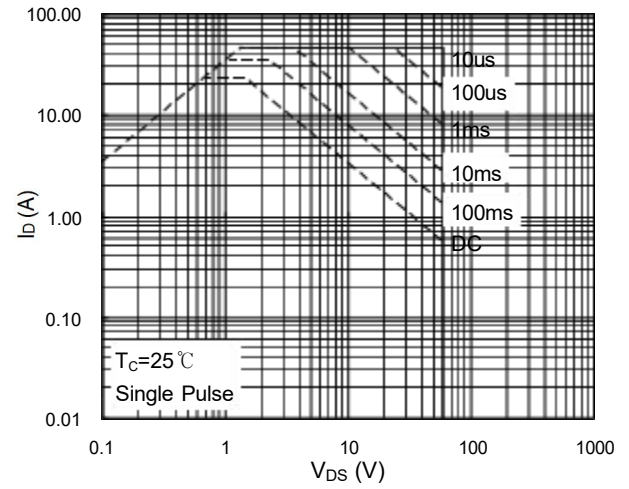


Fig.8 Safe Operating Area

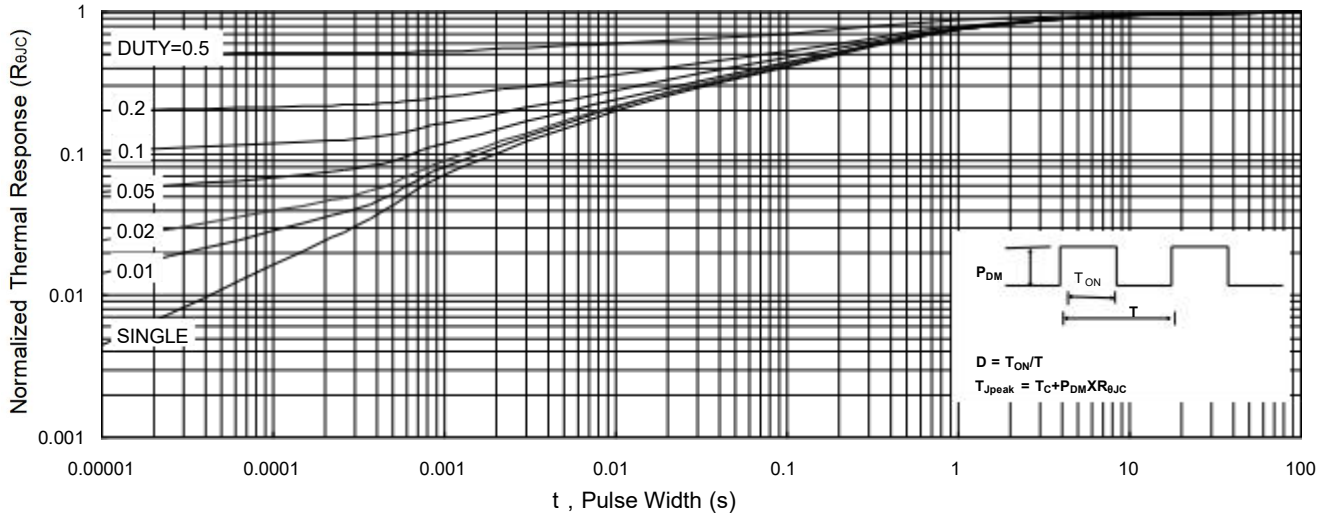


Fig.9 Normalized Maximum Transient Thermal Impedance

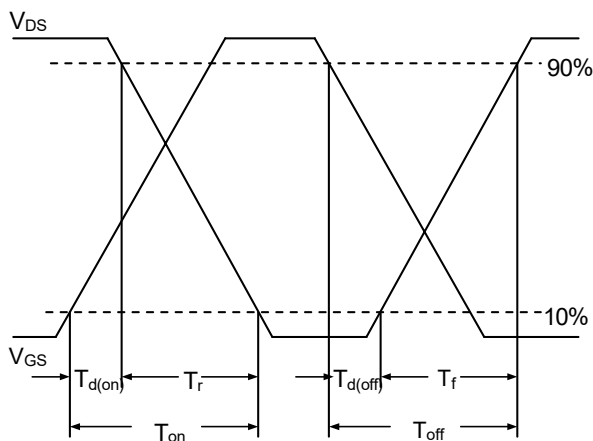


Fig.10 Switching Time Waveform

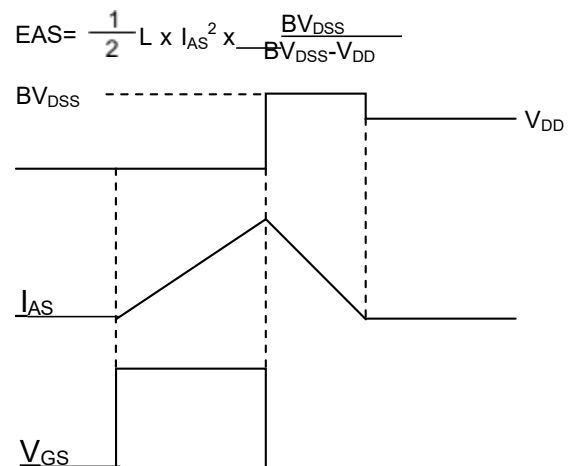


Fig.11 Unclamped Inductive Waveform

P-Channel Typical Characteristics

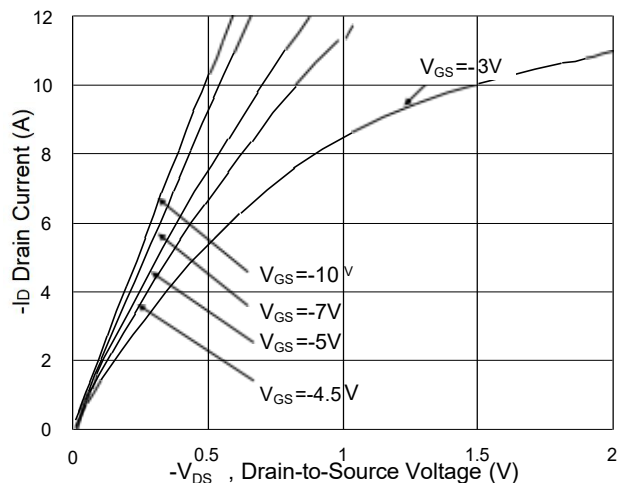


Fig.1 Typical Output Characteristics

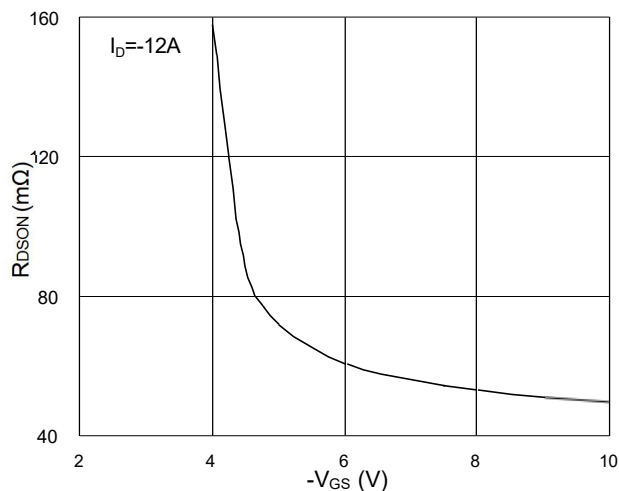


Fig.2 On-Resistance v.s Gate-Source

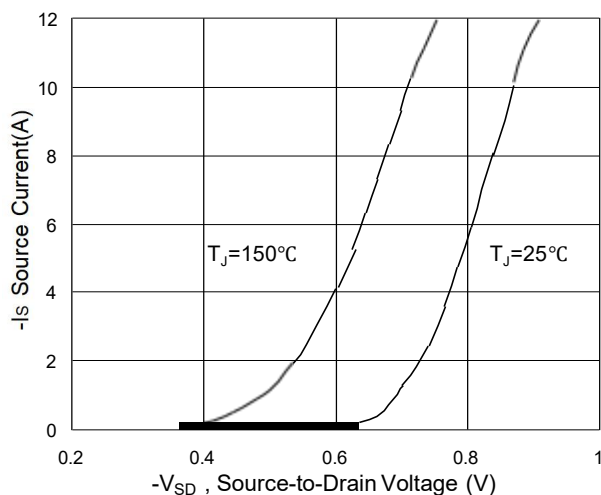


Fig.3 Forward Characteristics of Reverse

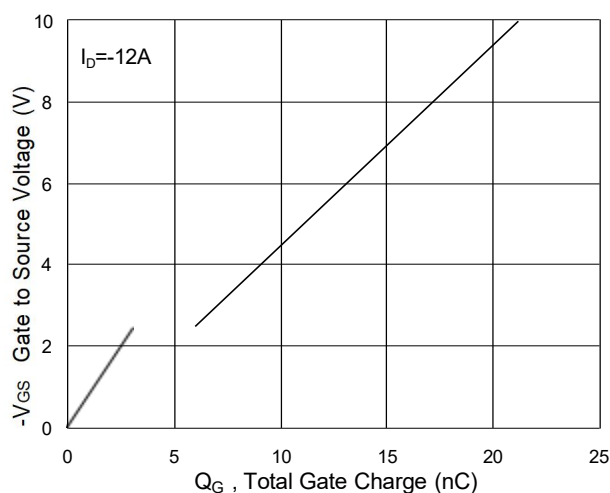


Fig.4 Gate-Charge Characteristics

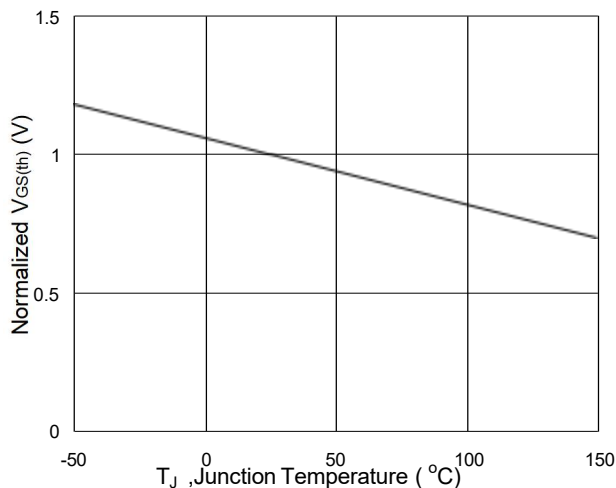


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

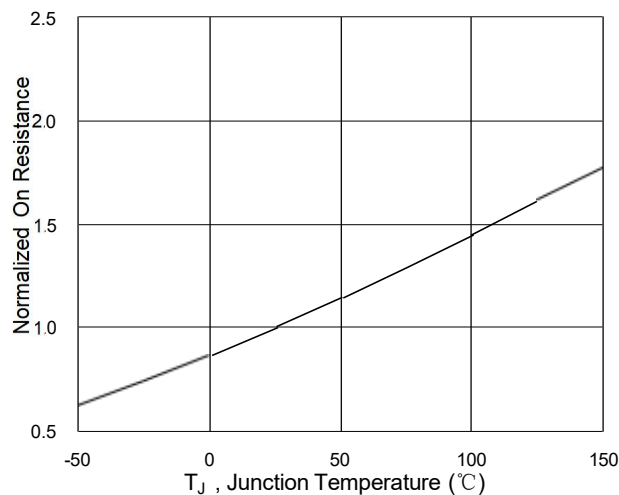


Fig.6 Normalized R_{DSON} v.s T_J

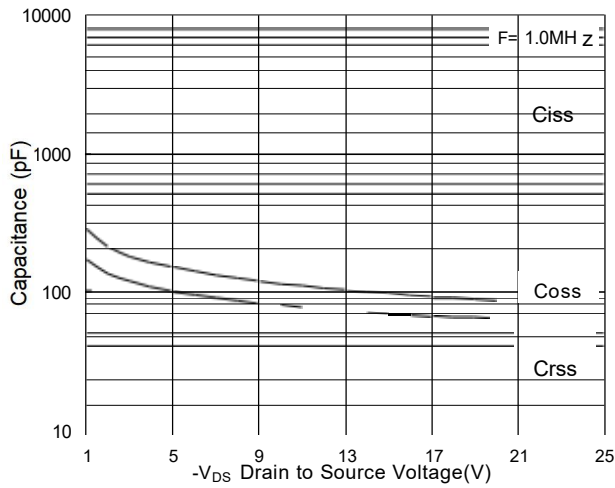


Fig.7 Capacitance

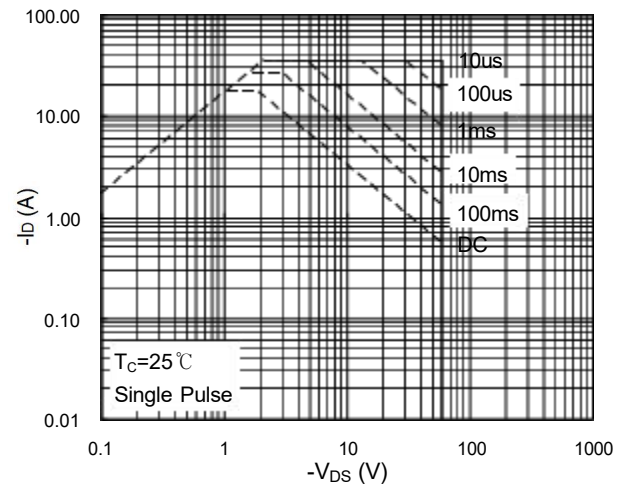


Fig.8 Safe Operating Area

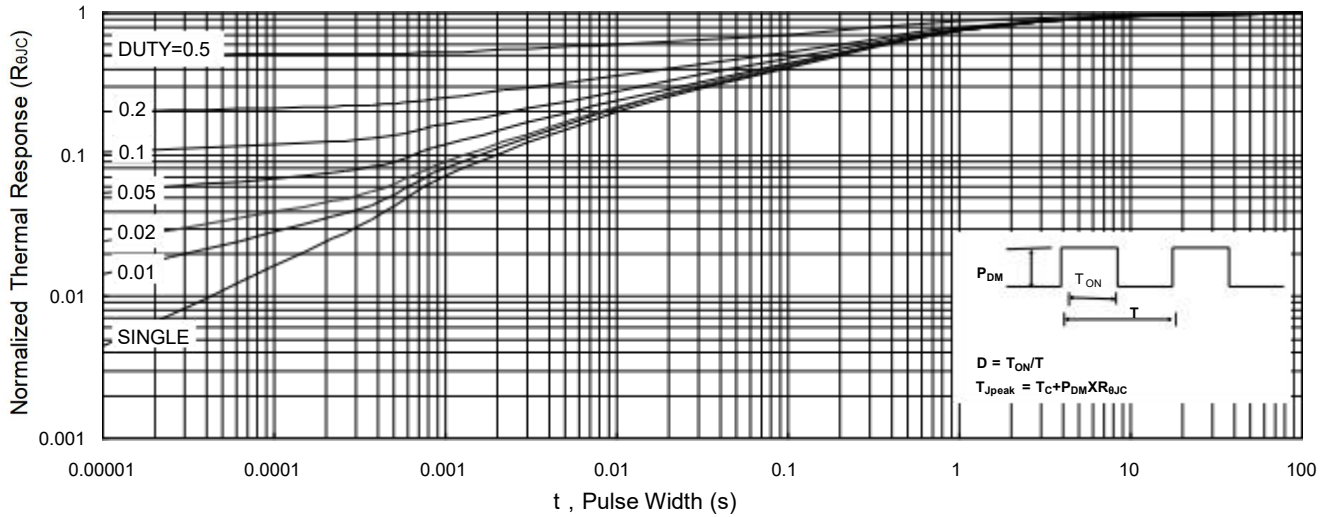


Fig.9 Normalized Maximum Transient Thermal Impedance

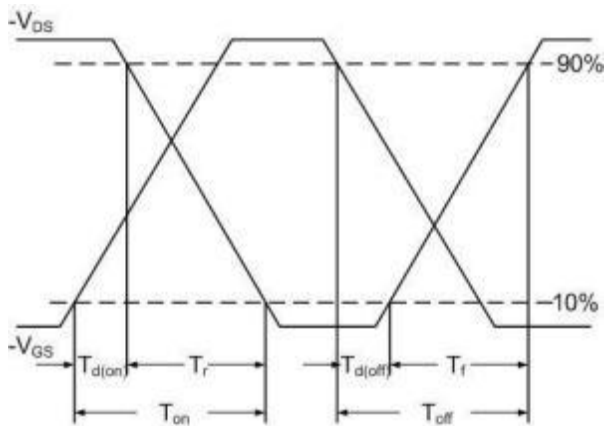


Fig.10 Switching Time Waveform

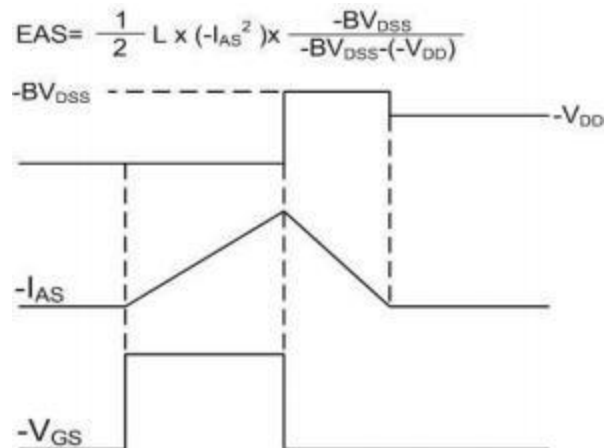


Fig.11 Unclamped Inductive Waveform

Package Mechanical Data-SOP-8

